



Sheet 2 of 2

29	10/689,990	10/22/2003	Kasuya		
FOREIGN PATENT DOCUMENTS					
	DOCUMENT NUMBER	DATE	COUNTRY	CLASS	SUB CLASS
CAL	30	JP A 2001-156188 (with abstract and translation)	06/08/2001	Japan	—
CAL	31	JP A 7-161851 (with abstract and translation)	06/23/1995	Japan	—
CAL	32	JP B1 2978477 (with translation)	09/10/1999	Japan	—
OTHER DOCUMENTS (Including Author, Title, Date, Pertinent Pages, etc.)					
CAL	33	Hayashi et al. "Twin MONOS Cell with Dual Control Gates", 2000 Symposium on VLSI Technology Digest of Technical Papers			
CAL	34	Chang et al. "A New SONOS Memory Using Source-Side Injection for Programming", IEEE Electron Device Letters, Vol. 19, No. 7, July 1998, pp 253-255			
CAL	35	Chen et al. "A Novel Flash Memory Device with S Plit Gate Source Side Injection and ONO Charge Storage Stack (SPIN), 1997 Symposium on VLSI Technology Digest of Technical Papers, pp 63-64			
 					
 					
 					
 					
 					
EXAMINER			DATE CONSIDERED		
C. J. [Signature]			6/10/05		
Examiner: Initial if citation considered, whether or not citation is in conformance with M.P.E.P. 609; draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.					

Date: March 24, 2004